Diode Semiconductor Device - Page 1 of 1



vor equipment, vol 8, sec 8, pg 8-38

| Inc | losure Material: |
|---|--|
| Me | tal |
| Ov | erall Length: |
| Be | tween 0.200 inches and 0.250 inches |
| 1.00 Ove 0.62 Fun Tran End 2gvo Mou | rminal Length: |
| | 100 inches |
| | erall Diameter: |
| | 25 inches |
| | nction For Which Designed: |
| | ansient suppressor |
| | d Application: |
| | vortac, fa-9996 |
| | ounting Method: |
| | rminal |
| | rminal Circle Diameter: |
| 0.0 | 151 inches |
| Se | miconductor Material: |
| Sili | icon |
| Vo | Itage Rating In Volts Per Characteristic: |
| 31. | 4 breakdown voltage, dc and 34.7 breakdown voltage, dc |
| Cu | rrent Rating Per Characteristic: |
| 40. | 00 milliamperes on-state current, dc |
| Sp | ecial Features: |
| Fu | nction, absorber, ovv; reference data, 1a2a2vr (typical), ti-6820.2, fa-9996, vortac, vor/dm |
| Те | rminal Type And Quantity: |
| 2 u | ininsulated wire lead |
| Sh | elf Life: |
| N/a | a |
| Un | it Of Measure: |
| | |
| De | militarization: |
| No | |
| Fiig | g: |
| A1 | 10a0 |